

#### **Features**

Low Power Consumption: 0.3uA (Typ)

Maximum Output Current: 500mA

 Small Dropout Voltage 100mV@100mA (Vout=3.3V)

PSRR=70dB@1KHz

• Input Voltage Range: 2.0V~7.0V

 Output Voltage Range: 0.8V~3.6V (customized on command in 0.05V steps)

• High Accurate: ±1.5%

- Integrated Short-Circuit Protection
- Good Transient Response
- Over-Temperature Protection
- Support Fixed Output Voltage
- Output Current Limit
- Stable with Ceramic Capacitor
- Available Package
   SOT23-3 \ SOT23-5 \ SOT89-3 \ DFN1x1-4L
- RoHS Compliant and Lead (Pb) Free

# **Application**

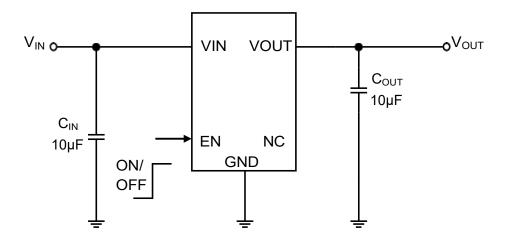
- Battery-powered equipment
- Reference voltage sources
- Mobile phones

- Cameras, video cameras
- Portable games

# **Description**

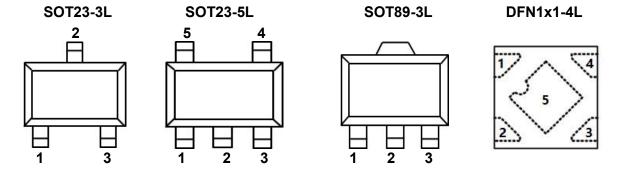
The WL9005 series are highly precise, low noise, positive voltage LDO regulators manufactured using CMOS processes. The series achieves high ripple rejection and low dropout and consists of a standard voltage source, an error correction, current limiter and a phase compensation circuit plus a driver transistor. Output voltage is selectable in 0.05V increments within a range of 0.8V  $\sim$  3.6V. The series is also compatible with low ESR ceramic capacitors which give added output stability. It provides up to 500mA of output current in miniaturized packaging. The features of low quiescent current as low as 0.3 $\mu$ A and almost zero disable current is ideal for powering the battery equipment to a longer service life. The other features include current limit function, Integrated Short-Circuit Protection , over temperature protection and output discharge function.

# **Application Circuits**





# **Pin Configuration**



# **Pin Description**

	Р	in No.		Die Neues Die Eurotien	
SOT23-3L	SOT23-5L	SOT89-3L	DFN1x1-4L	Pin Name	Pin Function
2	1	2	4	VIN	Supply voltage input.
1	2	1	2	GND	Ground.
	3		3	CE	Chip Enable
	4			NC	No Internal Connection.
3	5	3	1	VOUT	Voltage Output.
			5	SGND	Substrate of Chip. Leave floating or tie to GND.

# **Order Information**

## WL900512-34

Designator	Symbol	Description		
12	S3/S5/P3/D4	SOT23-3L / SOT23-5L / SOT89-3L / DFN1x1-4L		
34	Integer	Output Voltage (09、10、12、15、18、25、28、30、33、36)		

Model	Marking**	Description	Package	T/R Qty
WL9005S3-XX*			SOT23-3L	3,000 PCS
WL9005S5-XX*		WL9005 0.3µA IQ ,High PSRR	SOT23-5L	3,000 PCS
WL9005P3-XX*		500mA Low-Dropout LDO	SOT89-3L	1,000 PCS
WL9005D4-XX*			DFN1x1-4L	10,000 PCS

Note: (\*) XX Represents the Output Voltage

<sup>(\*\*)</sup> For marking information, contact our sales representative directly



# **Absolute Maximum Ratings** (1)(2)

Parameter		Symbol	Maximum Rating	Unit	
In must Valta ma		Vin	V <sub>SS</sub> -0.3~V <sub>SS</sub> +9.0	V	
Input Volta	age	Von/off	V <sub>SS</sub> -0.3~V <sub>IN</sub> +0.3	V	
Output Cur	rent	Іоит	550	mA	
Output Volt	age	Vouт	V <sub>SS</sub> -0.3~V <sub>IN</sub> +0.3	V	
	SOT23-3		400		
	SOT23-5	Pd	450	mW	
Power Dissipation	SOT89-3	F <b>u</b>	500	11100	
l oner Breerpanerr	DFN1x1-4L		400		
	SOT23-3		250	°C/W	
Thermal Resistance	SOT23-5	R <sub>0JA</sub> (3)	220	°C/W	
Thermal Resistance	SOT89-3	(Junction-to-ambient thermal resistance)	200	°C/W	
	DFN1x1-4L	(Junction-to-ambient thermal resistance)	250	°C/W	
Operating Temperature		Topr	-40~85	$^{\circ}\!\mathbb{C}$	
Storage Temperature		Tstg	-40~125	$^{\circ}\!\mathbb{C}$	
Soldering Temperature & Time		Tsolder	260℃, 10s		

Note (1): Exceeding these ratings may damage the device.

#### **ESD Ratings**

Item	Description	Value	Unit
	Human Body Model (HBM)		
V(ESD-HBM)	ANSI/ESDA/JEDEC JS-001-2014	±4000	V
	Classification, Class: 2		
	Charged Device Mode (CDM)		
V(ESD-CDM)	ANSI/ESDA/JEDEC JS-002-2014	±200	V
	Classification, Class: C0b		
l	JEDEC STANDARD NO.78E APRIL 2016	±150	mΛ
ILATCH-UP	Temperature Classification, Class: I	±150	mA

ESD testing is performed according to the respective JESD22 JEDEC standard. The human body model is a 100 pF capacitor discharged through a  $1.5k\Omega$  resistor into each pin. The machine model is a 200pF capacitor discharged directly into each pin.

#### **Recommended Operating Conditions**

Parameter	MIN.	MAX.	Units
Supply voltage at V <sub>IN</sub>	2.0	7.0	V
Operating junction temperature range, Tj	-40	125	°C
Operating free air temperature range, TA	-25	85	°C

Note: All limits specified at room temperature (TA = 25°C) unless otherwise specified. All room temperature limits are 100% production tested. All limits at temperature extremes are ensured through correlation using standard Statistical Quality Control (SQC) methods. All limits are used to calculate Average Outgoing Quality Level (AOQL).

Note (2): The device is not guaranteed to function outside of its operating conditions

Note (3): The package thermal impedance is calculated in accordance to JESD 51-7.



## **Electrical Characteristics**

(TestConditions:VIN=4.3V, Vout=3.3V,CIN=10uF, Cout=10uF,TA=25°C, unless otherwise specified.)

Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Voltage	Vin		2.0	_	7.0	V
Supply Current IQ		Vin > Vout ,EN=Vin Iload=0mA		0.3	0.7	uA
Standby Current	Іѕтву	V <sub>EN</sub> = 0			0.1	uA
Output Voltage	Vоит	V <sub>IN</sub> =V <sub>set</sub> +1.0V I <sub>OUT</sub> =100mA	Vset*0.985	Vset	Vset*1.015	V
Maximum Output Current	Іоит(Мах)	VIN=VOUT+1.0V		500		mA
Dropout Voltage	$V_{DROP^{(1)}}$	Iоит=100mA		100		mV
Dropout voltage	VDROP	Iоит=200mA		220		IIIV
Line Regulation	ΔVout/ ΔVin•Vout	Iουτ=10mA (Vset+0.5v)≦Vιν≦7.0V		0.1		%/V
Load Regulation	ΔVουτ	V <sub>IN</sub> =V <sub>set</sub> +1.0V 1mA≦I <sub>OUT</sub> ≦100mA		20		mV
Current Limit	Інміт		_	550	_	mA
Short Current	Ishort	RL=1Ω		90		mA
Power Supply	Denn	V <sub>IN</sub> =V <sub>set</sub> +1.0V f=1KHz,lout= 100mA		70		dB
Rejection Rate	PSRR	V <sub>IN</sub> =V <sub>set</sub> +1.0V f=10KHz,I <sub>OUT</sub> = 100mA		65		dB
EN Threshold	VIL	VIN=3V~ 5.5V, Shutdown			0.4	
Voltage	Vih	V <sub>IN</sub> =3V~ 5.5V, Start-Up	1.2			
Output Noise Voltage	<b>е</b> мо	Co∪т=1uF BW = 100Hz~10kHz		100		uVRMS
Output Voltage Temperature Coefficient	ΔVουτ/ ΔΤ•Vουτ	Iоит=3 <b>0mA</b>		±100		ppm/℃
Thermal Shutdown Temperature	Tsp			160	_	$^{\circ}$
Thermal Shutdown Hysteresis	ΔTsb		_	20	_	$^{\circ}$

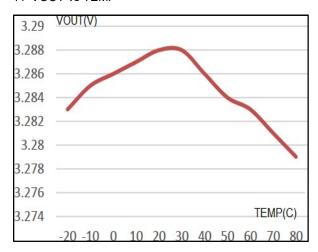
Note: (1) Dropout Voltage is the voltage difference between the input and the output at which the output voltage drops 2% below its nominal value.



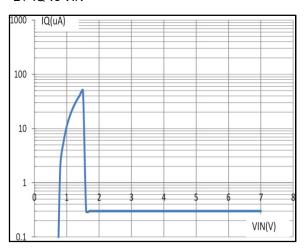
# **Typical Performance Characteristics**

Test Condition: T<sub>A=</sub>25°C, unless otherwise note

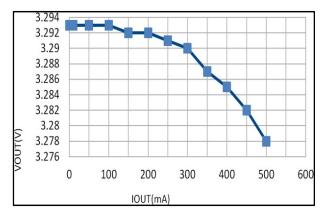
#### 1、VOUT vs TEMP



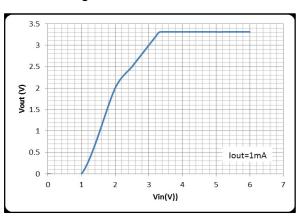
2、IQ vs VIN (※)



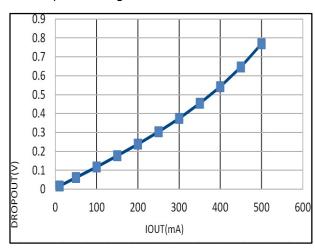
#### 3. Load Regulation



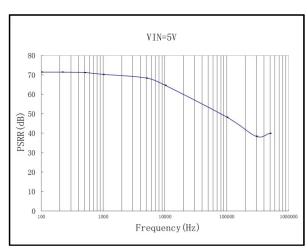
4. Line Regulation



#### 5. Dropout Voltage vs Load Current



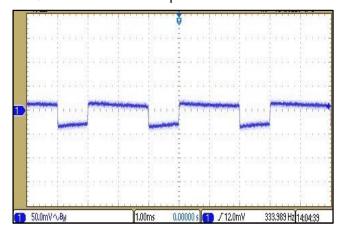
#### 6、PSRR



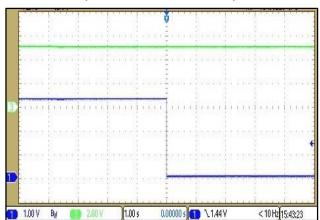
Note: (\*)IQ refers to the working current when the chip is no-load, only when Vin >vout The chip will have a very low working current, the above diagram is for Vout 1.5v Measured Curve, when Vin<Vout, the chip is in an abnormal state that can not reach the intended output, therefore, the operating current will increase significantly. For applications where IQ requirements are strict, make sure the chip stops working when Vin <Vout.



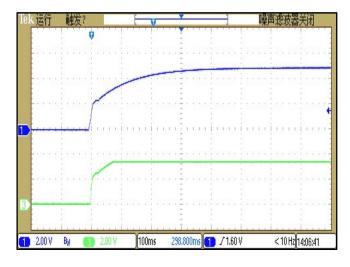
#### 7、Load Transient Response



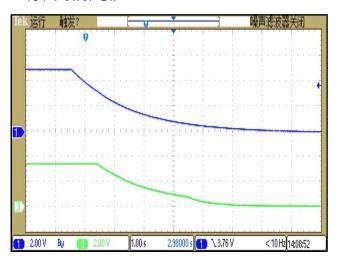
#### 8. Short Output & Over-Current Response



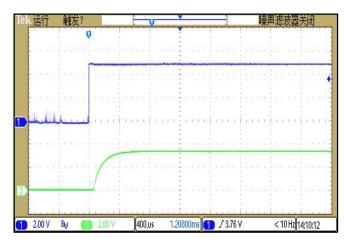
#### 9、Power-On



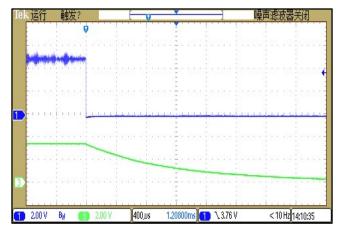
10 Power-Off



11、Enable

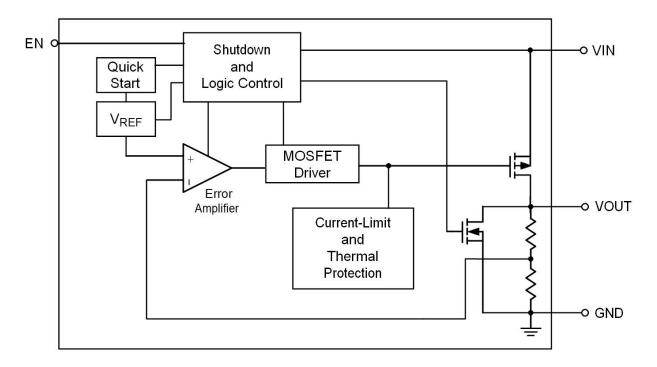


12、Disable





#### **Function Block Diagram**



### **Application Guideline**

#### **Input Capacitor**

A  $1\mu F$  ceramic capacitor is recommended to connect between  $V_{DD}$  and GND pins to decouple input power supply glitch and noise. The amount of the capacitance may be increased without limit. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both VIN and GND.

#### **Output Capacitor**

An output capacitor is required for the stability of the LDO. The recommended output capacitance is 10µF, ceramic capacitor is recommended, and temperature characteristics are X7R or X5R. Higher capacitance values help to improve load/line transient response. The output capacitance may be increased to keep low undershoot/overshoot. Place output capacitor as close as possible to VOUT and GND pins.

#### **Dropout Voltage**

The dropout voltage refers to the voltage difference between the VIN and VOUT pins while operating at specific output current. The dropout voltage VDROP also can be expressed as the voltage drop on the pass-FET at specific output current (IRATED) while the pass-FET is fully operating at ohmic



region and the pass-FET can be characterized as an resistance RDS(ON). Thus the dropout voltage can be defined as (VDROP = VIN - VOUT = RDS(ON) x IRATED). For normal operation, the suggested LDO operating range is (VIN > VOUT + VDROP) for good transient response and PSRR ability. Vice versa, while operating at the ohmic region will degrade the performance severely.

#### **Thermal Application**

For continuous operation, do not exceed the absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated as below: TA=25°C, PCB,

The max PD= (125°C - 25°C) / (Thermal Resistance °C/W)

Power dissipation (PD) is equal to the product of the output current and the voltage drop across the output pass element, as shown in the equation below:

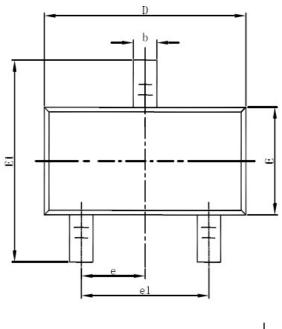
 $PD = (VIN - VOUT) \times IOUT$ 

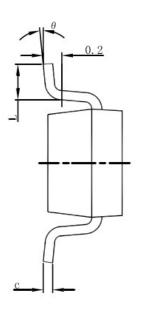
#### **Layout Consideration**

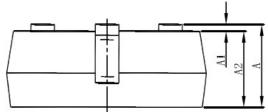
By placing input and output capacitors on the same side of the PCB as the LDO, and placing them as close as is practical to the package can achieve the best performance. The ground connections for input and output capacitors must be back to the WL9005 ground pin using as wide and as short of a copper trace as is practical. Connections using long trace lengths, narrow trace widths, and/ or connections through via must be avoided. These add parasitic inductances and resistance that results in worse performance especially during transient conditions.



## SOT23-3L



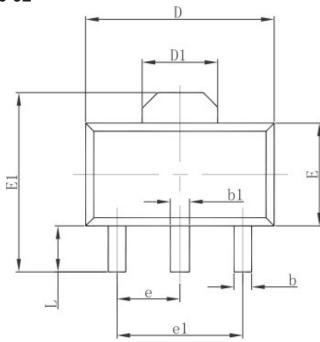


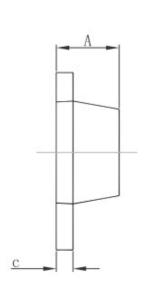


Symbol	Dimensions In	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950	(BSC)	0.037(	BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°



## **SOT89-3L**

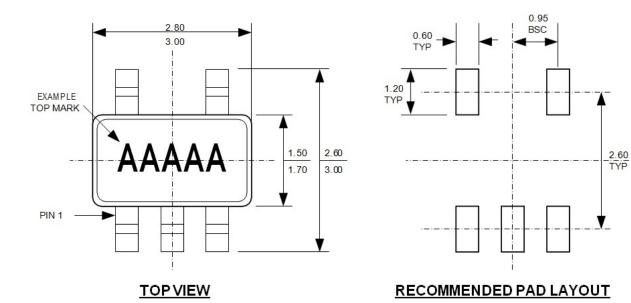




C b l	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min.	Max.	Min.	Max.
Α	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
С	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550	REF.	0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
е	1.500 TYP.		0.060	TYP.
e1	3.000 TYP.		0.118	TYP.
1	0.900	1 200	0.035	0.047

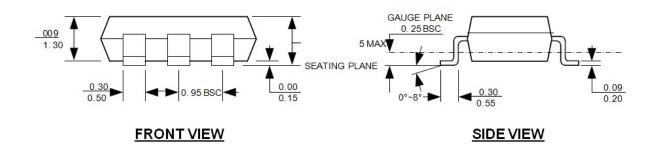


#### SOT23-5L



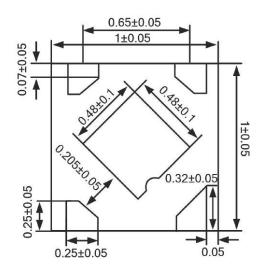
#### **TOP VIEW**

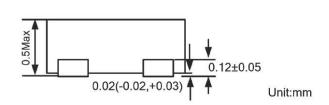
#### RECOMMENDED PAD LAYOUT





### DFN1x1-4L





Detail A: (PIN1 shape)





Unit:mm